

60V N-Channel Enhancement Mode MOSFET

Voltage	60 V	R _{DSON}	3.3 mΩ
Current	131 A	Q _G (TYP)	99 nC

Feature

- R_{DSON}, V_{GS}@10V, I_D@40A<3.3mΩ
- R_{DSON}, V_{GS}@7V, I_D@10A<5.4mΩ
- High switching speed
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN5060-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0028 ounces, 0.08 grams

Application

- BMS, BLDC motor driver switch, Load Switch.

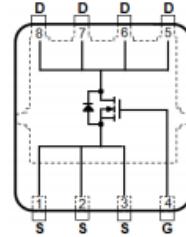
Absolute Maximum Ratings (T_A = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	+20/ -12	
Continuous Drain Current (Note 3)	T _C =25°C	I _D	A
	T _C =100°C		
Pulsed Drain Current	T _C =25°C	I _{DM}	A
Single Pulse Avalanche Current (Note 5)	I _{AS}	62	A
Single Pulse Avalanche Energy (Note 5)	E _{AS}	192	mJ
Power Dissipation	T _C =25°C	P _D	W
	T _C =100°C		
Operating Junction and Storage Temperature Range	T _{J,T STG}	-55~150	°C

Thermal Characteristics

PARAMETER	SYMBOL	MAXIMUM	UNITS
Thermal Resistance	R _{θJC}	1.3	°C/W
	R _{θJT}	21	°C/W
	R _{θJA}	50	°C/W

DFN5060-8L



Top side view

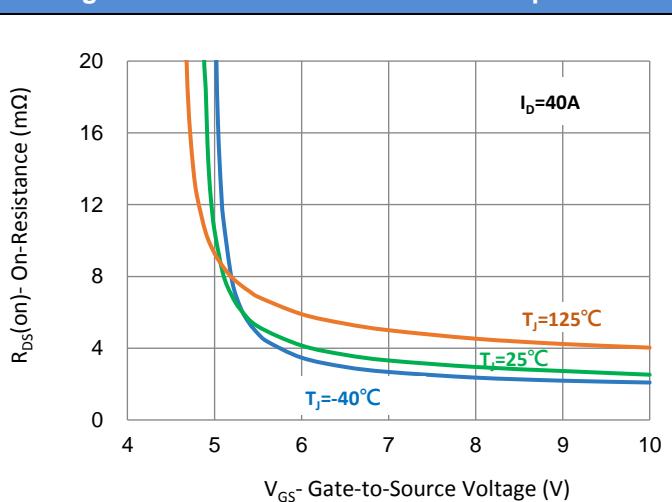
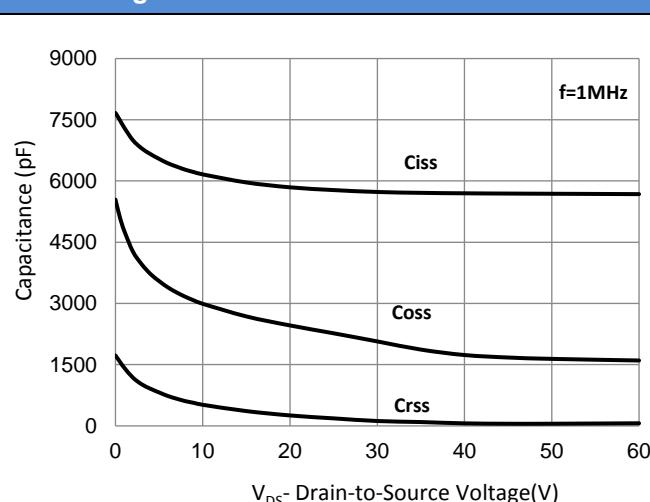
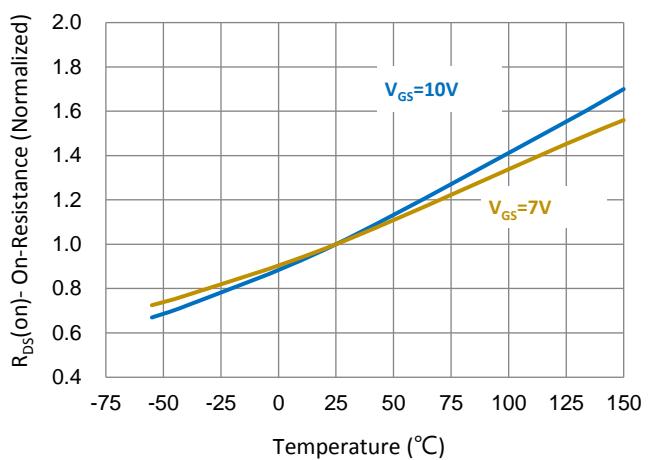
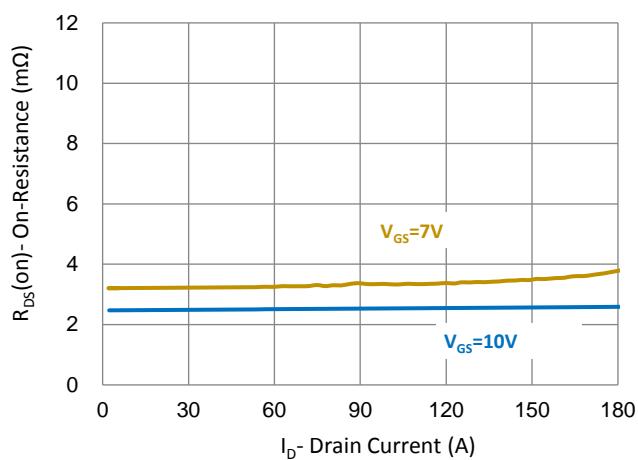
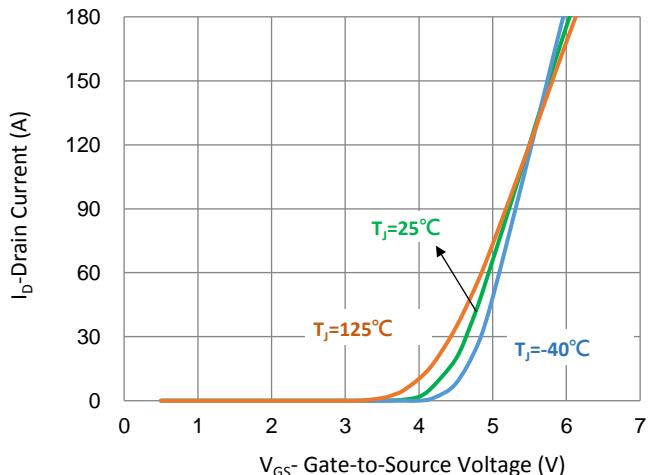
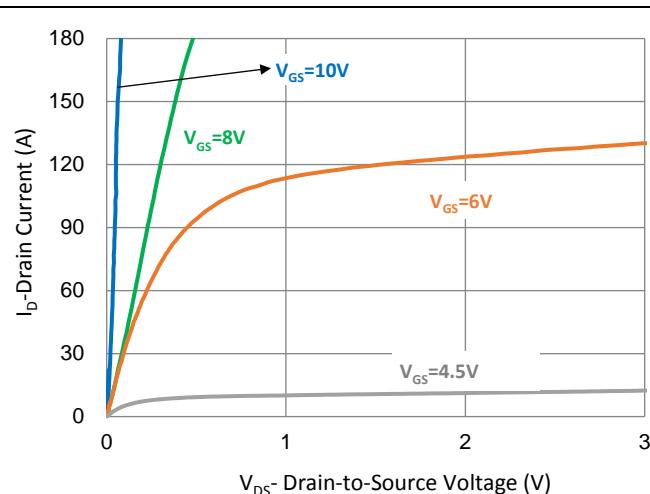
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	60	-	-	V
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	2	3	4	
Drain-Source On-State Resistance (Note 1)	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=40\text{A}$	-	2.5	3.3	$\text{m}\Omega$
		$V_{\text{GS}}=7\text{V}, I_{\text{D}}=10\text{A}$	-	3.2	5.4	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	100	nA
Transfer characteristics (Note 1)	g_{fs}	$V_{\text{DS}}=3\text{V}, I_{\text{D}}=20\text{A}$	-	71	-	S
Dynamic (Note 6)						
Total Gate Charge	Q_g	$V_{\text{DS}}=30\text{V}, I_{\text{D}}=40\text{A}, V_{\text{GS}}=7\text{V}$	-	74	-	nC
Gate-Source Charge	Q_{gs}	$V_{\text{DS}}=30\text{V}, I_{\text{D}}=40\text{A}, V_{\text{GS}}=10\text{V}$	-	99	-	
Gate-Drain Charge	Q_{gd}		-	26	-	
Plateau Voltage	V_{GP}		-	29	-	
Input Capacitance	C_{iss}	$V_{\text{DS}}=30\text{V}, V_{\text{GS}}=0\text{V}, f=1.0\text{MHz}$	-	4.8	-	V
Output Capacitance	C_{oss}		-	5731	-	pF
Reverse Transfer Capacitance	C_{rss}		-	2070	-	
Turn-On Delay Time	$t_{\text{d(on)}}$	$V_{\text{DD}}=30\text{V}, I_{\text{D}}=40\text{A}, V_{\text{GS}}=10\text{V}, R_{\text{G}}=2\Omega$ (Note 2)	-	61	-	ns
Turn-On Rise Time	t_r		-	106	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	106	-	
Turn-Off Fall Time	t_f		-	59	-	
Gate Resistance	R_g	$f = 1.0\text{MHz}$	0.5	1.7	3	Ω
Drain-Source Diode						
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=1\text{A}, V_{\text{GS}}=0\text{V}$	-	0.7	1	V
Reverse Recovery Charge	Q_{rr}	$I_{\text{SD}} = 40\text{A}$	-	42	-	nC
Reverse Recovery Time	T_{rr}	$di/dt = 100\text{A}/\mu\text{s}$	-	52	-	ns

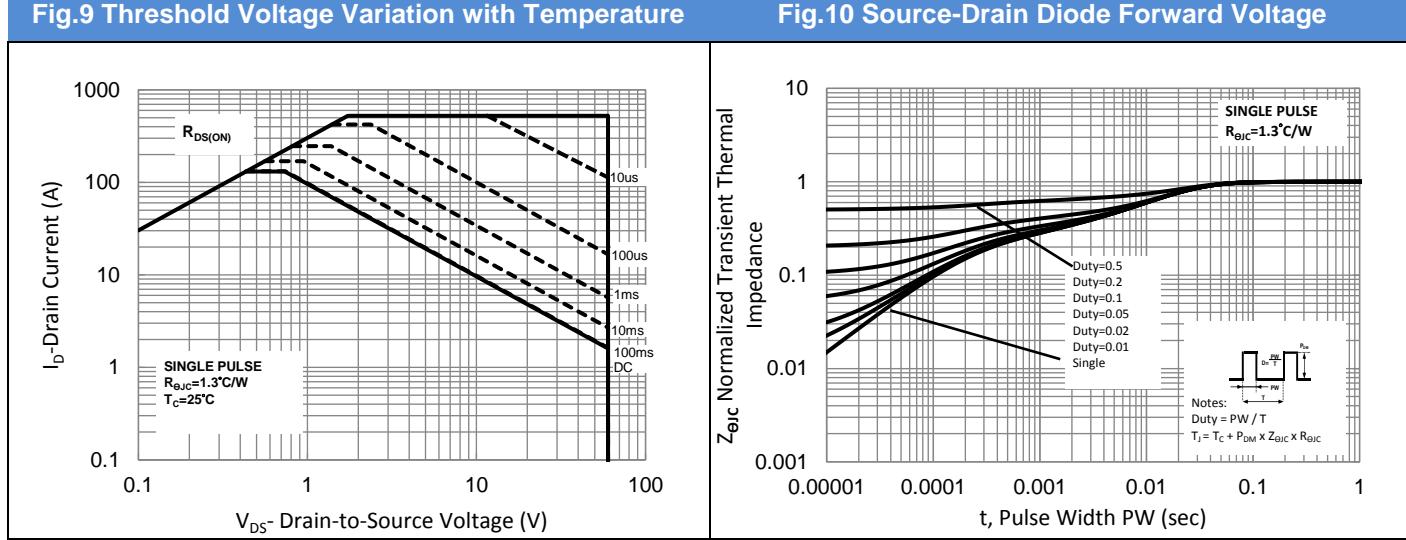
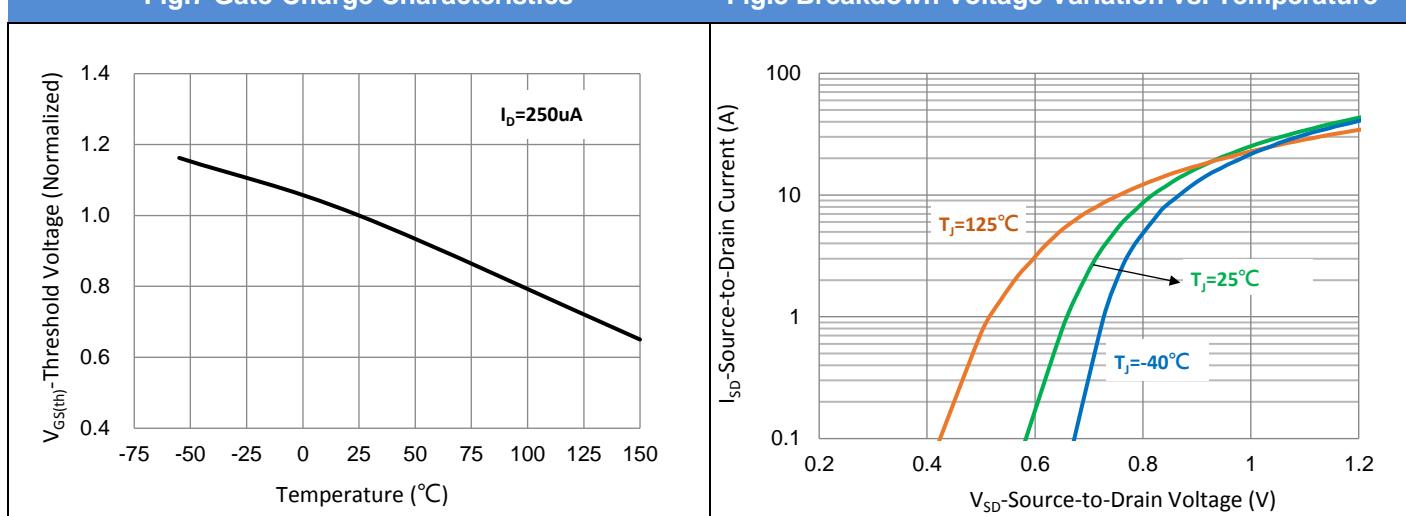
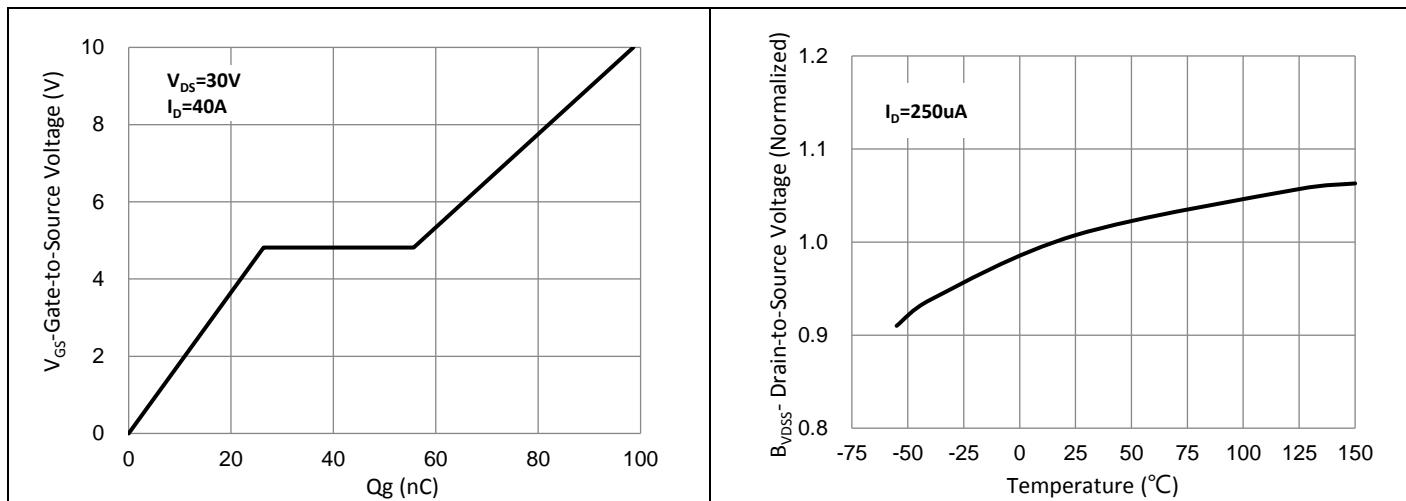
NOTES :

1. Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. The maximum current rating is silicon limited.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
5. The test condition is $L=0.1\text{mH}, I_{AS}=62\text{A}, V_{DD}=25\text{V}, V_{GS}=10\text{V}, R_G=25\text{ohm}$, Starting $T_J=25^\circ\text{C}$
6. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTIC CURVES



TYPICAL CHARACTERISTIC CURVES



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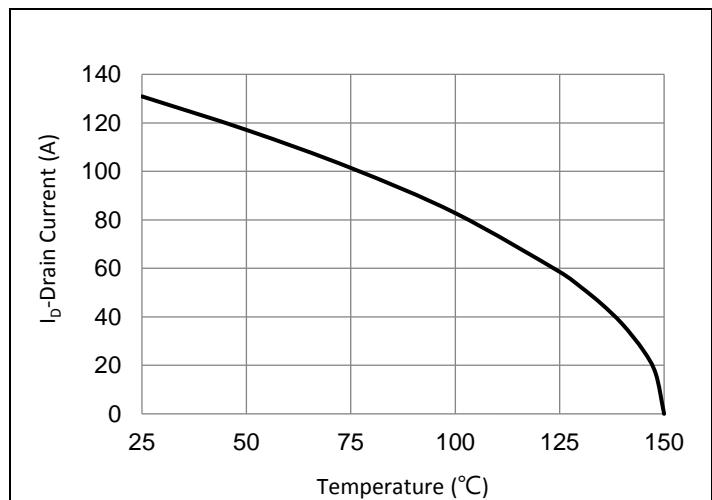
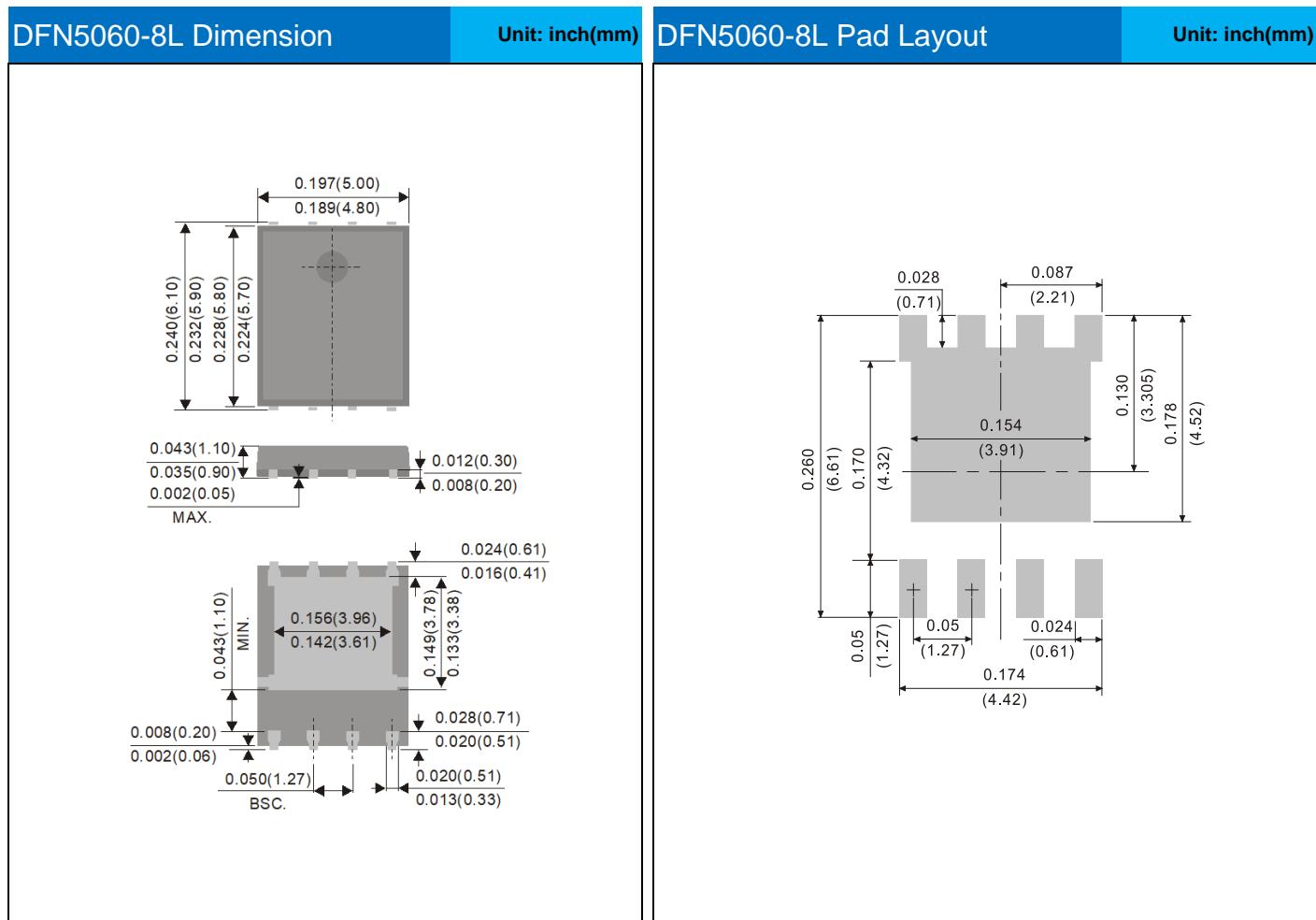


Fig.13 Drain Current vs. Case Temperature

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PSMQC033N06NS1	DFN5060-8L	3000pcs / 13" reel	033N06NS

Packaging Information & Mounting Pad Layout



Marking Diagram

PJ
033N06NS
YWLL X

Y = Year Code
W = Week Code (A~Z)
LL = Lot Code (00~99)
x = Production Line Code

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